



High and Low Side Driver

November 2018

PRODUCT SUMMARY

• V_{OFFSET}	600 V max.
• $I_{O+/-}$	1.4A/1.8A
• V_{OUT}	10 V - 20 V
• $t_{on/off}$ (typ.)	220 ns/200 ns
• Deadtime (typ.)	none

GENERAL DESCRIPTION

The SLM2106B is a high voltage, high speed power MOSFET and IGBT drivers with independent high- and low-side referenced output channels.

Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

FEATURES

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V, 5 V, and 15 V logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5 V offset
- Lower di/dt gate driver for better noise immunity
- Outputs in phase with inputs
- RoHS compliant
- SOIC-8 and PDIP-8 package

TYPICAL APPLICATION CIRCUIT

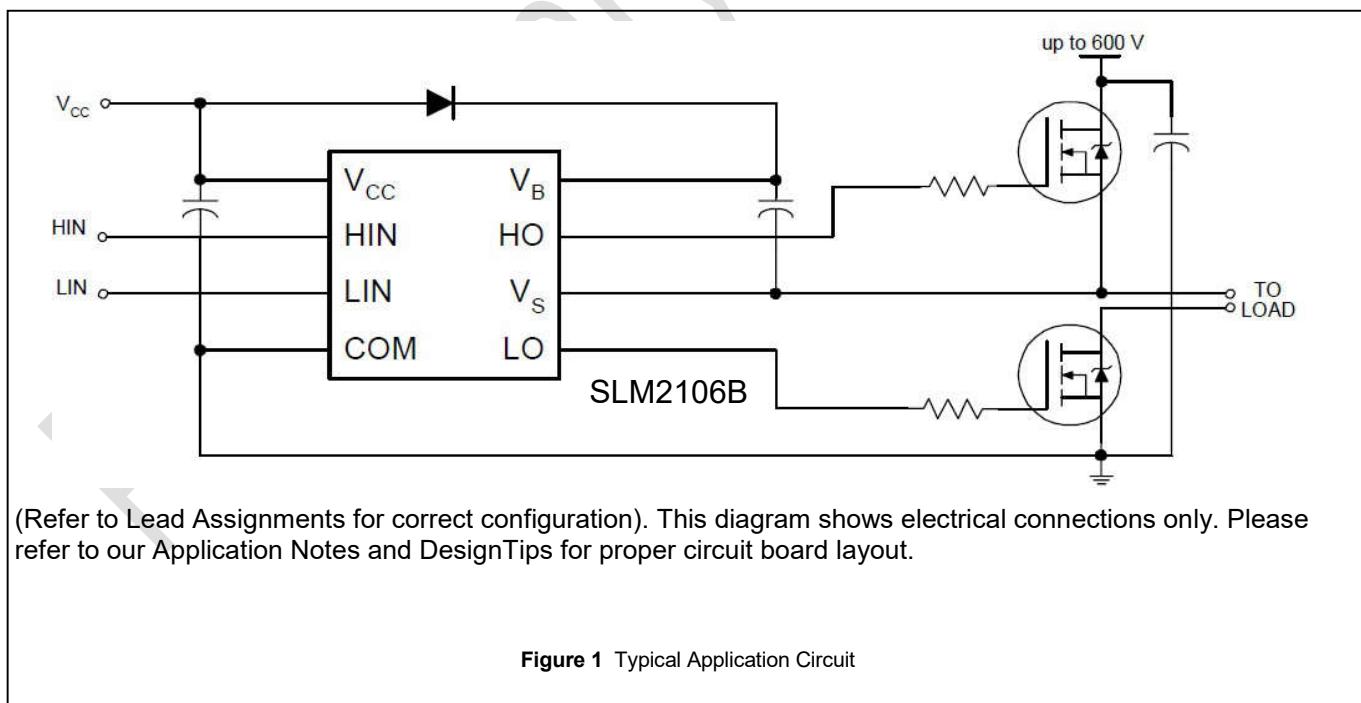
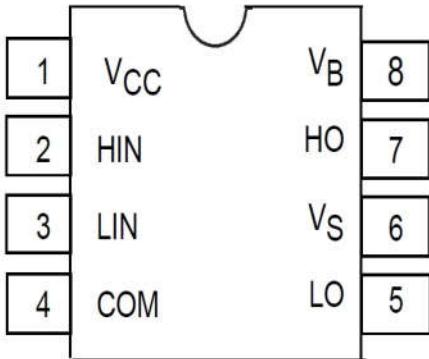


Figure 1 Typical Application Circuit



PIN CONFIGURATION

Package	Pin Configuration (Top View)
SOIC-8 and PDIP-8	

PIN DESCRIPTION

No.	Pin	Description
1	V _{CC}	Low-side and logic fixed supply
2	HIN	Logic input for high-side gate driver output (HO), in phase
3	LIN	Logic input for low-side gate driver output (LO), in phase
4	COM	Low-side return
5	LO	Low-side gate drive output
6	V _S	High-side floating supply return
7	HO	High-side gate drive output
8	V _B	High-side floating supply

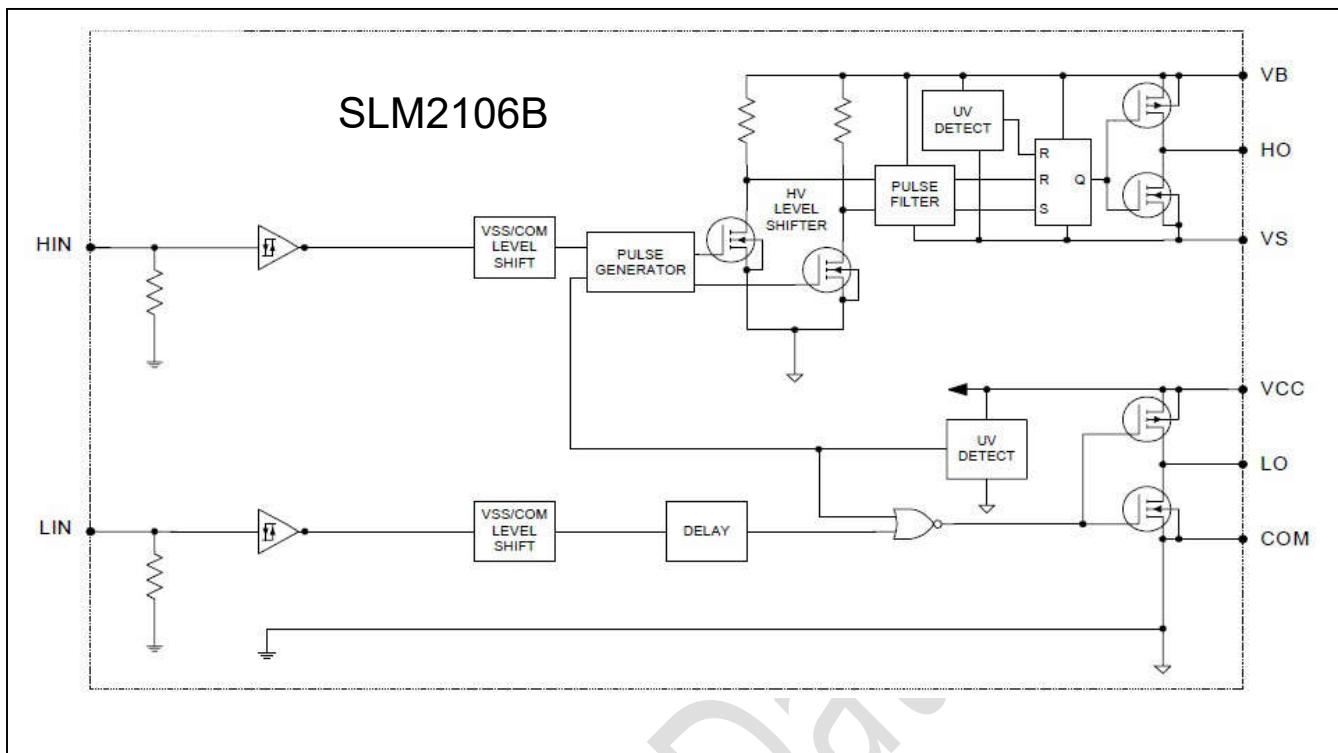
ORDERING INFORMATION

Industrial Range: -40°C to +125°C

Order Part No.	Package	QTY
SLM2106BCA-13GTR	SOIC8, Pb-Free	2500/Reel
SLM2106BCA-GT	SOIC8, Pb-Free	100/Tube
SLM2106BDA-GT	PDIP8, Pb-Free	100/Tube



FUNCTIONAL BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS

Symbol	Definition	Min.	Max.	Units
V_B	High-side floating absolute voltage	-0.3	625	V
V_S	High-side floating supply offset voltage	$V_B - 25$	$V_B + 0.3$	
V_{HO}	High-side floating output voltage	$V_S - 0.3$	$V_B + 0.3$	
V_{CC}	Low-side and logic fixed supply voltage	-0.3	25	
V_{LO}	Low-side output voltage	-0.3	$V_{CC} + 0.3$	
V_{IN}	Logic input voltage (HIN & LIN)	-0.3	$V_{CC} + 0.3$	
dV_S/dt	Allowable offset supply voltage transient	---	50	V/ns
P_D	Package power dissipation @ $T_A \leqslant +25^\circ\text{C}$	PDIP-8	---	1.0
		SOIC-8	---	0.625
R_{thJA}	Thermal resistance, junction to ambient	PDIP-8	---	125
		SOIC-8	---	200
T_J	Junction temperature	---	150	$^\circ\text{C}/\text{W}$
T_S	Storage temperature	-55	150	
T_L	Lead temperature (soldering, 10 seconds)	---	300	

Note:

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

RECOMMENDED OPERATION CONDITIONS

Symbol	Definition	Min.	Max.	Units
V_B	High-side floating absolute voltage	$V_S + 10$	$V_S + 20$	V
V_S	High-side floating supply offset voltage	Note 1	600	
V_{HO}	High-side floating output voltage	V_S	V_B	
V_{CC}	Low-side and logic fixed supply voltage	10	20	
V_{LO}	Low-side output voltage	0	V_{CC}	
V_{IN}	Logic input voltage	V_{SS}	V_{CC}	
T_A	Ambient temperature	-40	125	$^\circ\text{C}$

Note:

The input/output logic timing diagram is shown in Fig. 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at a 15 V differential.



DYNAMIC ELECTRICAL CHARACTERISTICS

 V_{BIAS} (V_{CC} , V_{BS}) = 15 V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
t_{on}	Turn-on propagation delay	$V_S = 0$ V	---	220	300	ns
t_{off}	Turn-off propagation delay	$V_S = 0$ V or 600 V	---	200	280	
t_r	Turn-on rise time	$V_S = 0$ V	---	40	220	
t_f	Turn-off fall time		---	15	80	
MT	Delay matching, HS & LS turn-on/off		---	0	30	

STATIC ELECTRICAL CHARACTERISTICS

 V_{BIAS} (V_{CC} , V_{BS}) = 15 V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} , and I_{IN} parameters are referenced to COM. The V_o and I_o parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
V_{IH}	Logic "1" input voltage	$V_{CC} = 10$ V to 20V	2.5	---	---	V
V_{IL}	Logic "0" input voltage		---	---	0.8	
V_{OH}	High level output voltage, $V_{BIAS} - V_o$	$I_o = 2$ mA	---	0.05	0.2	
V_{OL}	Low level output voltage, V_o		---	0.02	0.1	
I_{LK}	Offset supply leakage current	$V_B = V_S = 600$ V	---	---	50	μA
I_{QBS}	Quiescent V_{BS} supply current	$V_{IN} = 0$ V or 5 V	20	75	130	
I_{QCC}	Quiescent V_{CC} supply current		60	120	180	
I_{IN+}	Logic "1" input bias current $V_{IN} = 5$ V		---	5	20	
I_{IN-}	Logic "0" input bias current $V_{IN} = 0$ V		---	---	5	
V_{CCUV+}	V_{CC} supply undervoltage positive going threshold		7.2	8.0	8.9	V
V_{CCUV-}	V_{CC} supply undervoltage negative going threshold		6.4	7.2	8.0	
V_{BSUV+}	V_{BS} supply undervoltage positive going threshold		6.4	7.2	8.0	
V_{BSUV-}	V_{BS} supply undervoltage negative going threshold		5.8	6.6	7.4	
I_{O+}	Output high short circuit pulsed current	$V_o = 0$ V, $PW \leq 10$ μs		1.4		A
I_{O-}	Output low short circuit pulsed current	$V_o = 15$ V, $PW \leq 10$ μs		1.8		

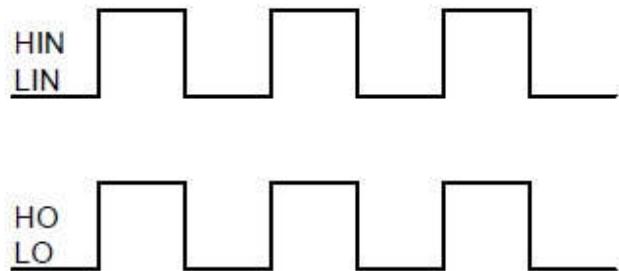


Figure 1. Input/Output Timing Diagram

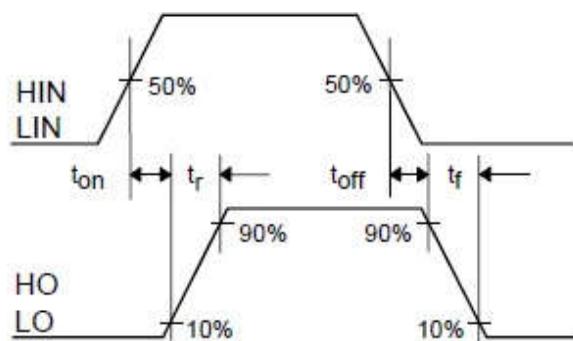


Figure 2. Switching Time Waveform Definitions

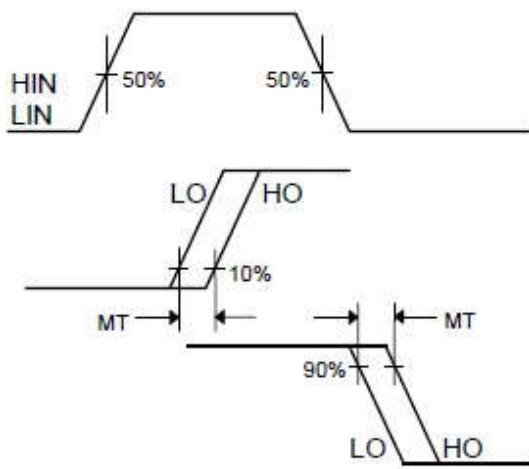


Figure 3. Delay Matching Waveform Definitions

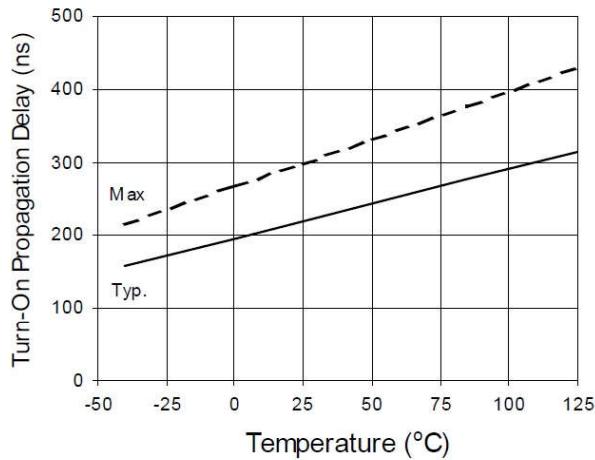


Figure 4A. Turn-On Propagation Delay
vs. Temperature

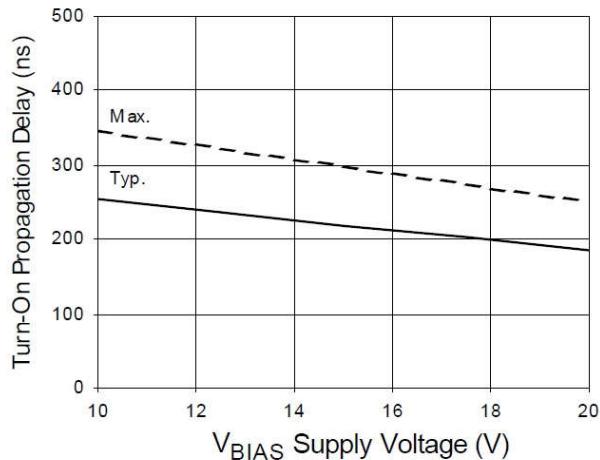


Figure 4B. Turn-On Propagation Delay
vs. Supply Voltage

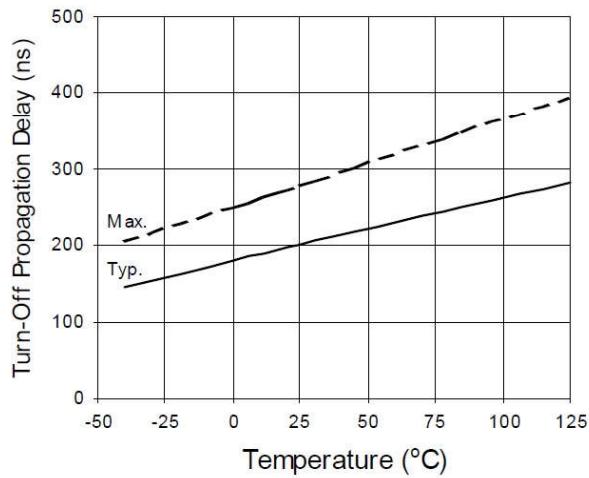


Figure 5A. Turn-Off Propagation Delay
vs. Temperature

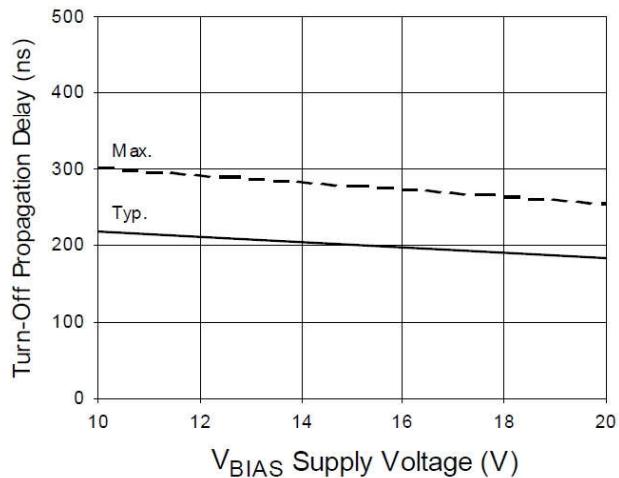


Figure 5B. Turn-Off Propagation Delay
vs. Supply Voltage

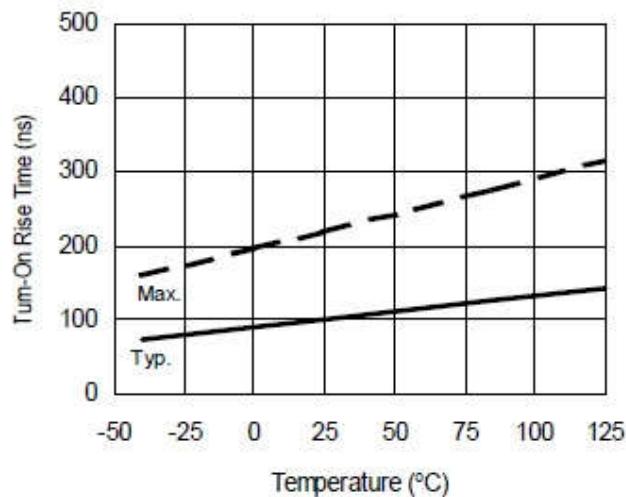


Figure 6A. Turn-On Rise Time vs. Temperature

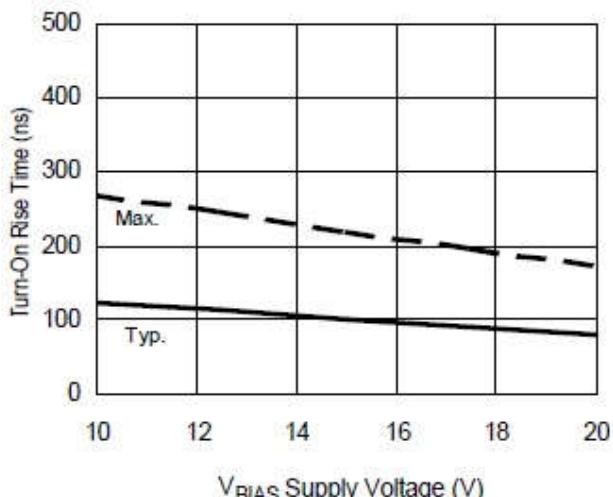


Figure 6B. Turn-On Rise Time vs. Supply Voltage

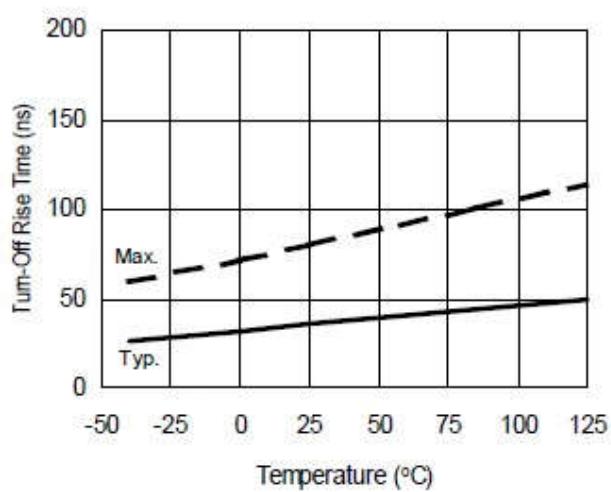


Figure 7A. Turn-Off Fall Time vs. Temperature

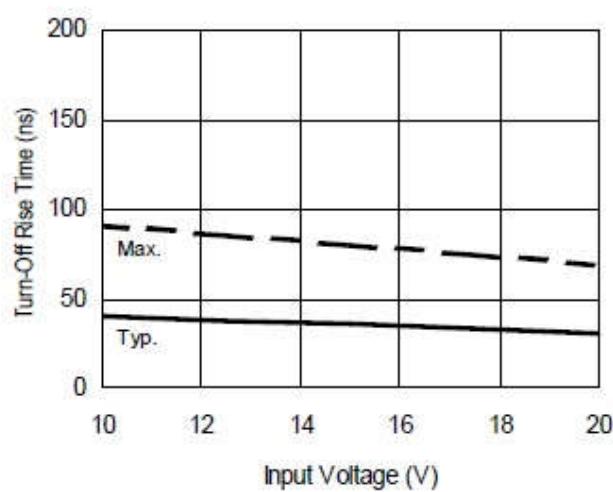


Figure 7B. Turn-Off Fall Time vs. Supply Voltage

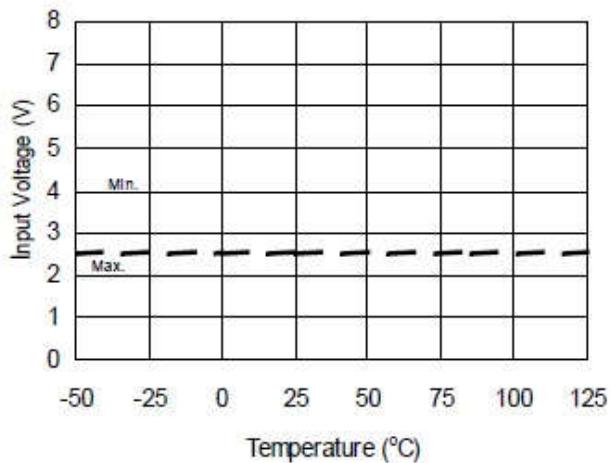


Figure 8A. Logic "1" Input Voltage
vs. Temperature

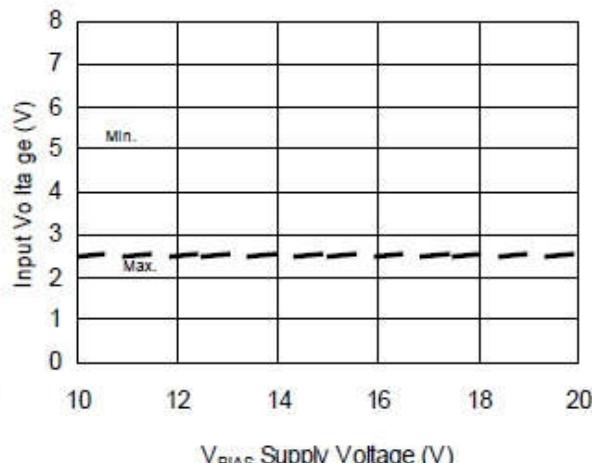


Figure 8B. Logic "1" Input Voltage
vs. Supply Voltage

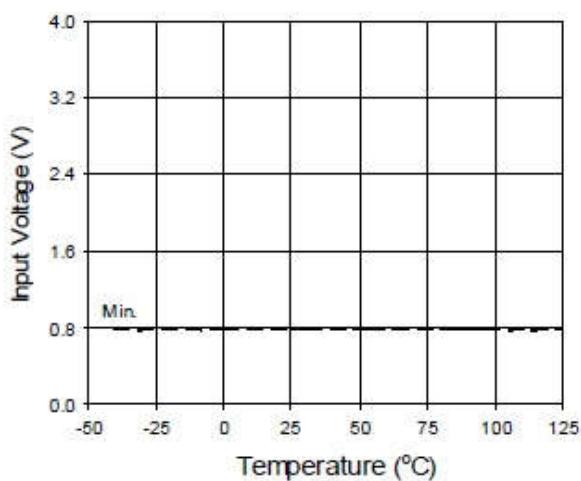


Figure 9A. Logic "0" Input Voltage
vs. Temperature

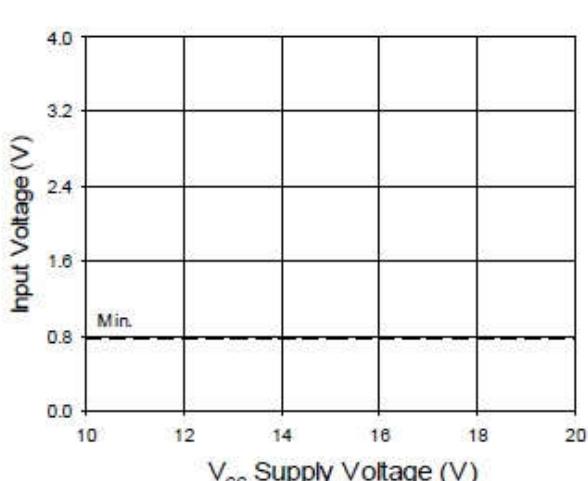


Figure 9B. Logic "0" Input Voltage
vs. Supply Voltage

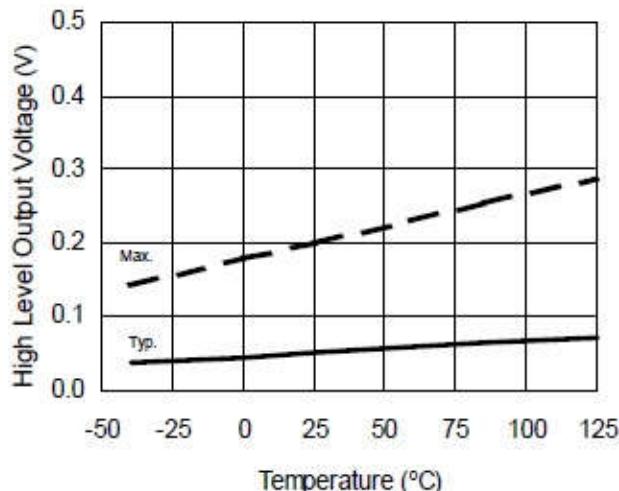


Figure 10A. High Level Output Voltage vs. Temperature

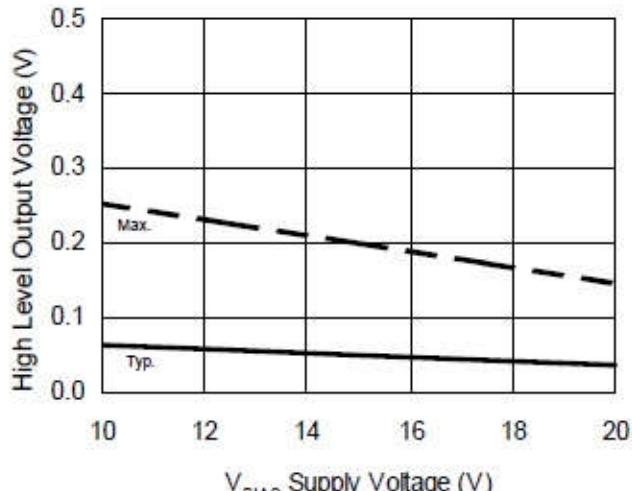


Figure 10B. High Level Output Voltage vs. Supply Voltage

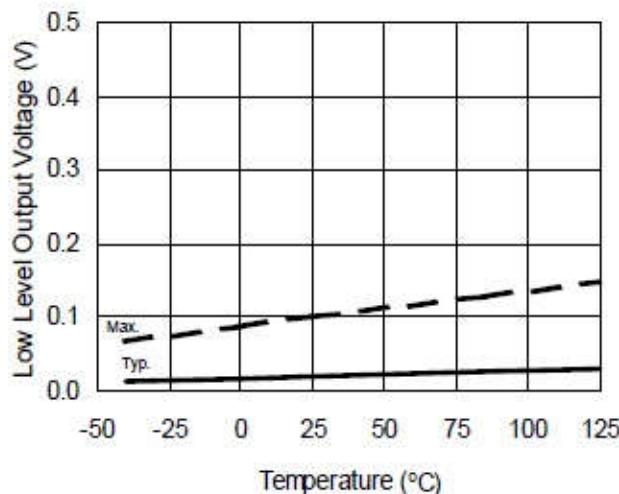


Figure 11A. Low Level Output Voltage vs. Temperature

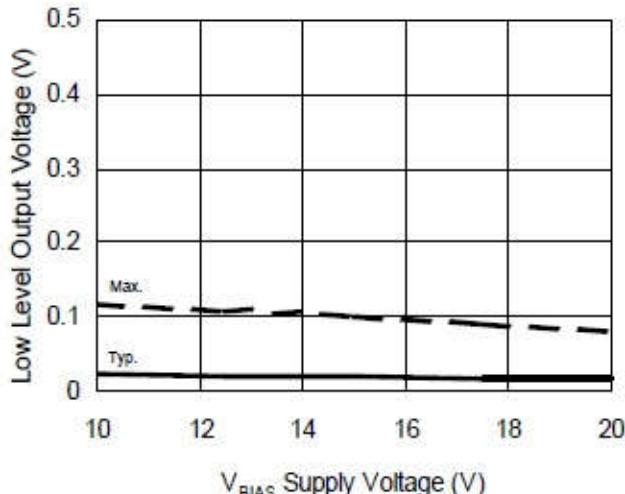


Figure 11B. Low Level Output Voltage vs. Supply Voltage

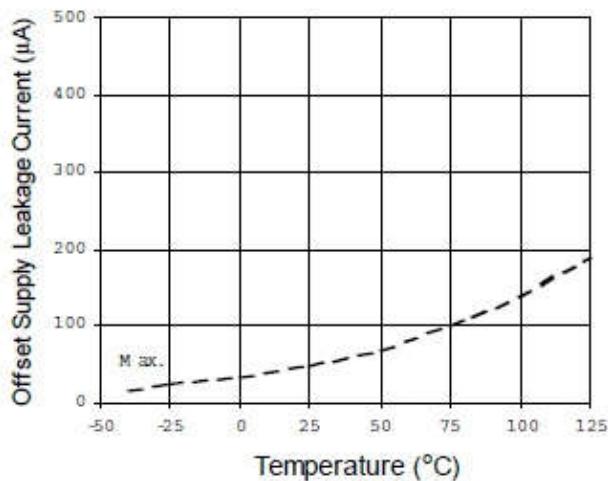


Figure 12A. Offset Supply Leakage Current vs. Temperature

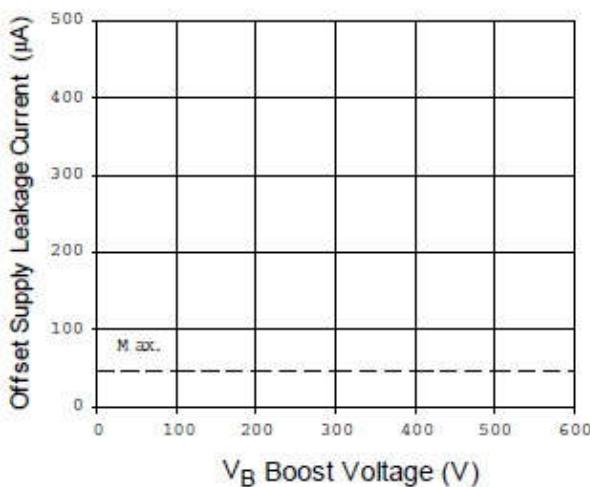


Figure 12B. Offset Supply Leakage Current vs. Supply Voltage

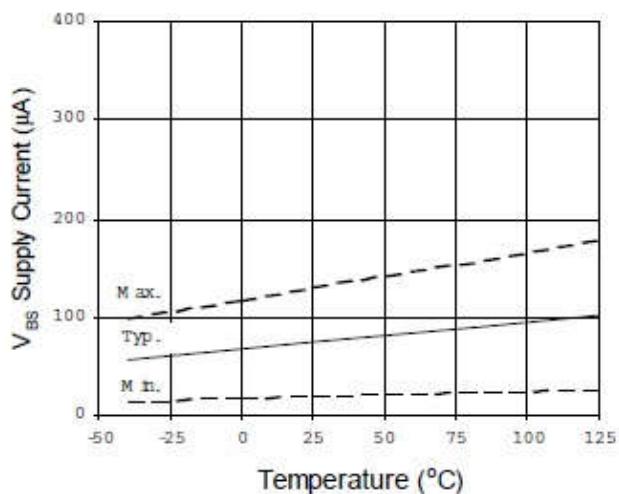


Figure 13A. V_{BS} Supply Current vs. Temperature

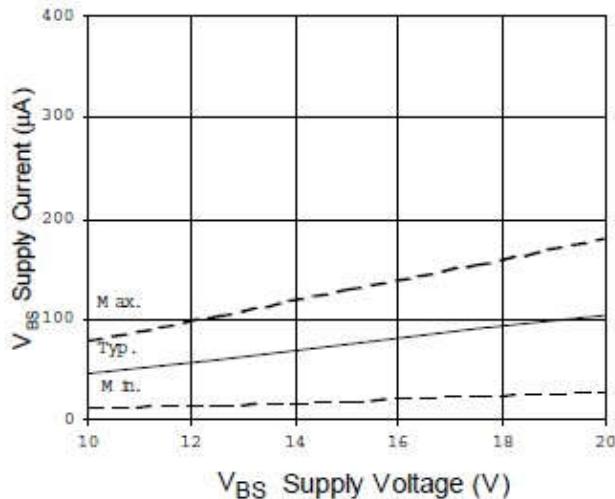


Figure 13B. V_{BS} Supply Current vs. Supply Voltage

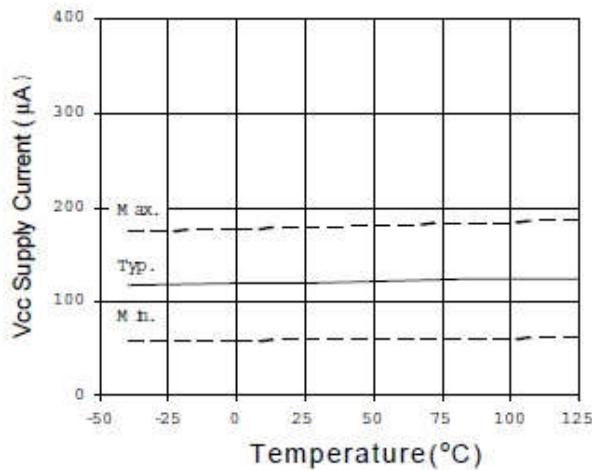


Figure 14A. Quiescent V_{CC} Supply Current vs. Temperature

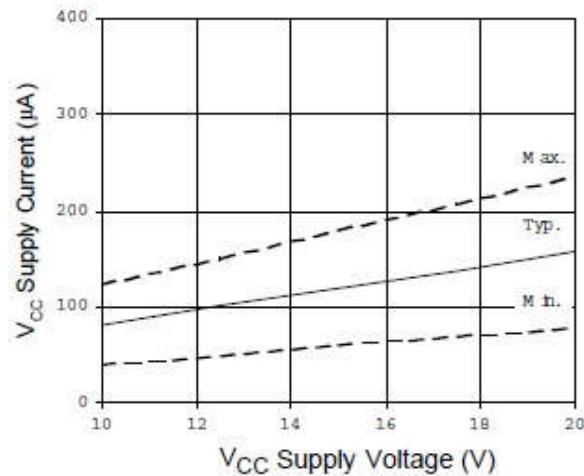


Figure 14B. Quiescent V_{CC} Supply Current vs. V_{CC} Supply Voltage

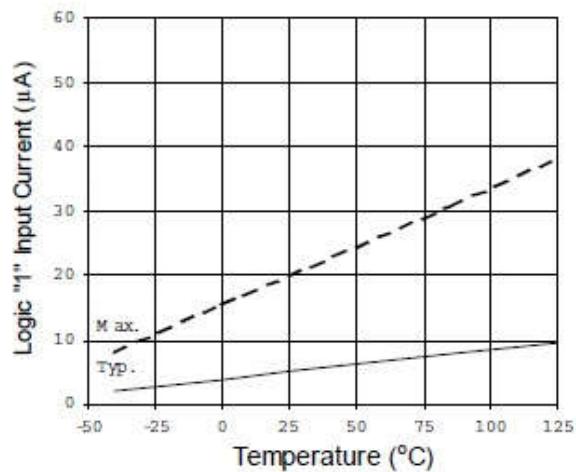


Figure 15A. Logic "1" Input Current vs. Temperature

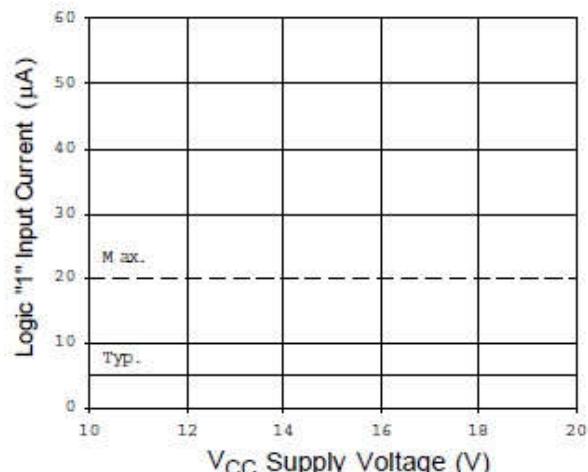


Figure 15B. Logic "1" Bias Current vs. Supply Voltage

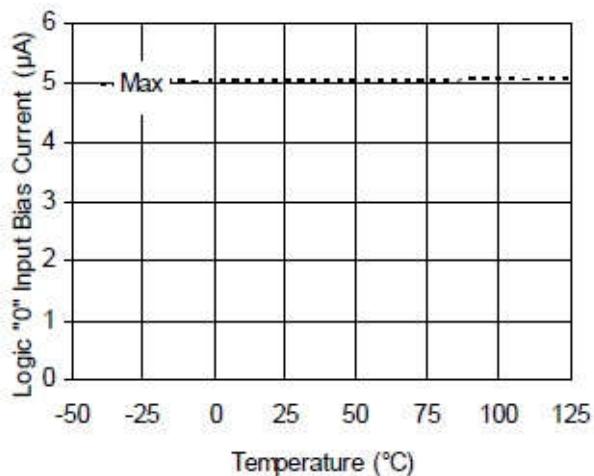


Figure 16A. Logic "0" Input Bias Current
vs. Temperature

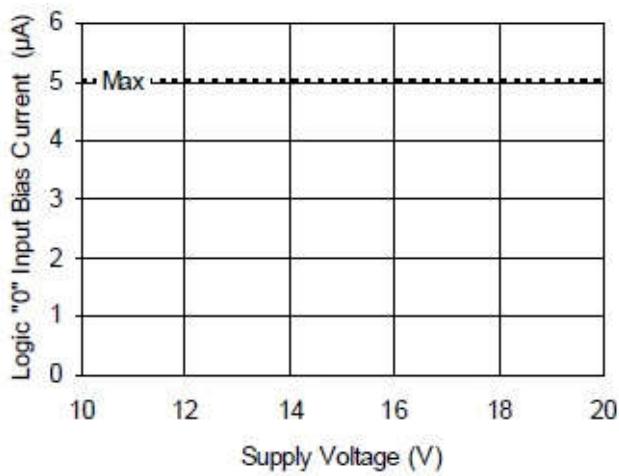


Figure 16B. Logic "0" Input Bias Current
vs. Voltage

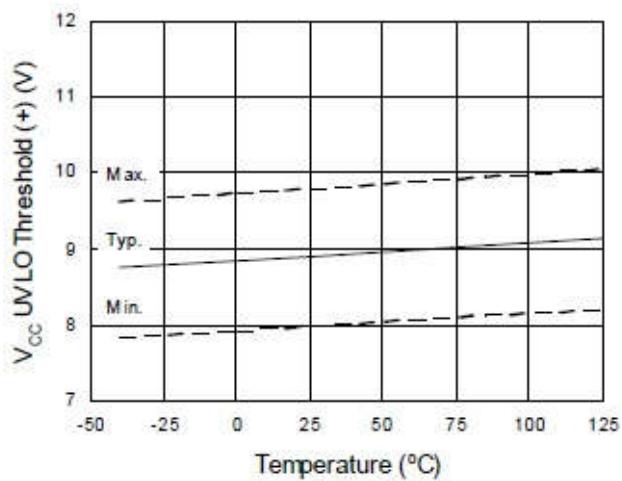


Figure 17. V_{CC} Undervoltage Threshold (+)
vs. Temperature

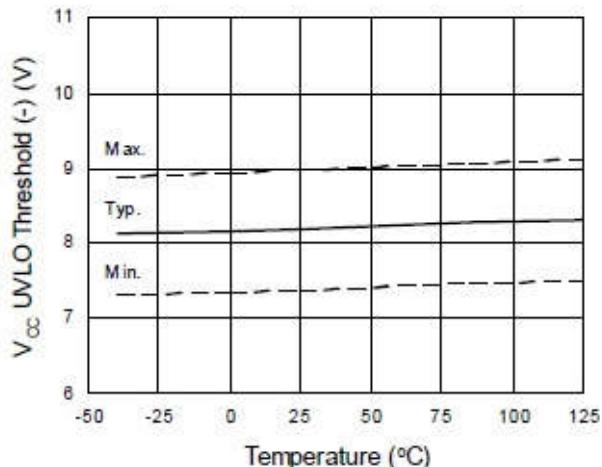


Figure 18. V_{CC} Undervoltage Threshold (-)
vs. Temperature

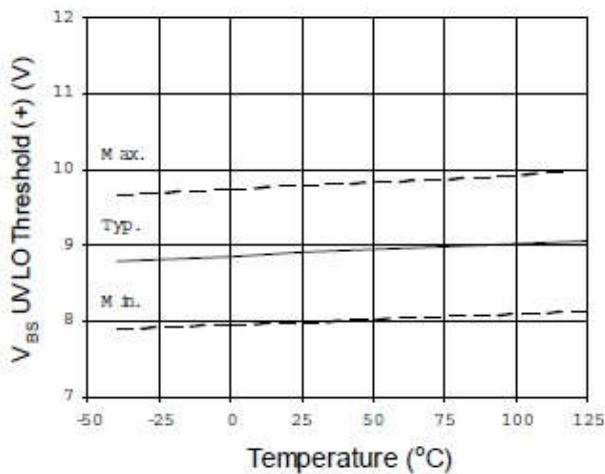


Figure 19. V_{B5} Undervoltage Threshold (+)
vs. Temperature

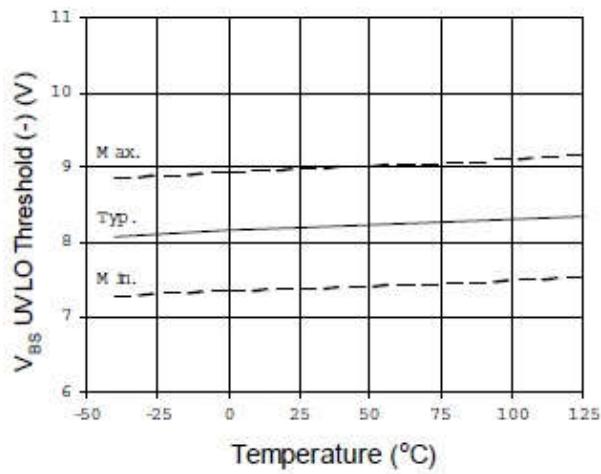


Figure 20. V_{B5} Undervoltage Threshold (-)
vs. Temperature

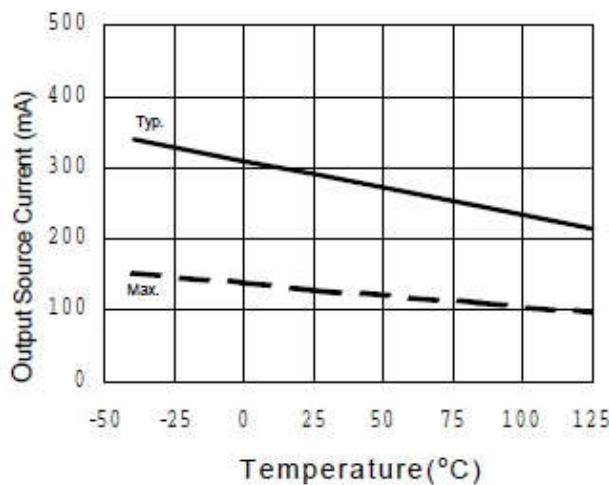


Figure 21A. Output Source Current
vs. Temperature

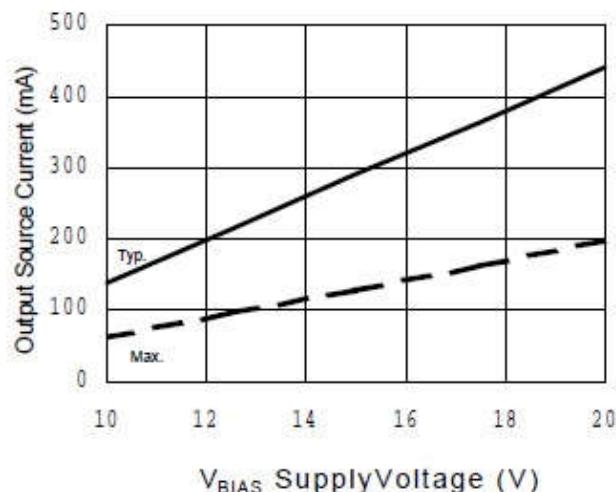


Figure 21B. Output Source Current
vs. Supply Voltage

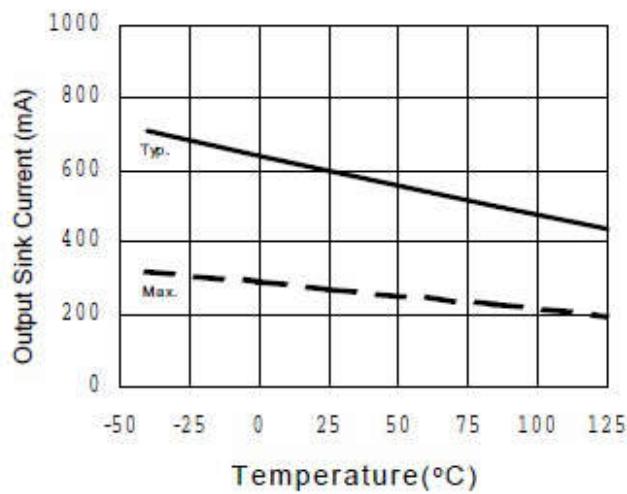


Figure 22A. Output Sink Current
vs. Temperature

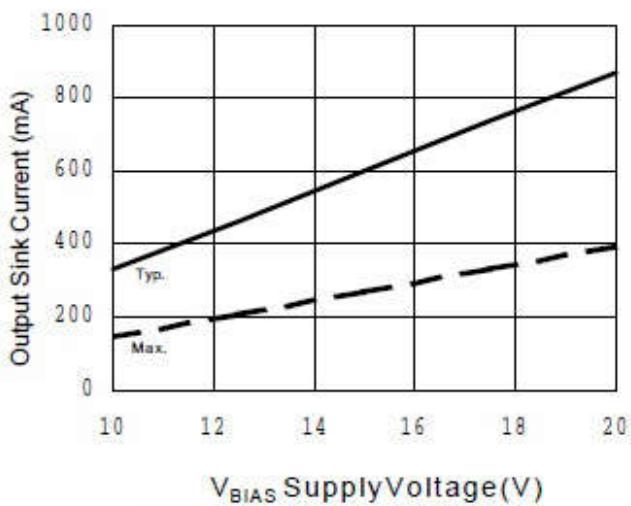


Figure 22B. Output Sink Current
vs. Supply Voltage

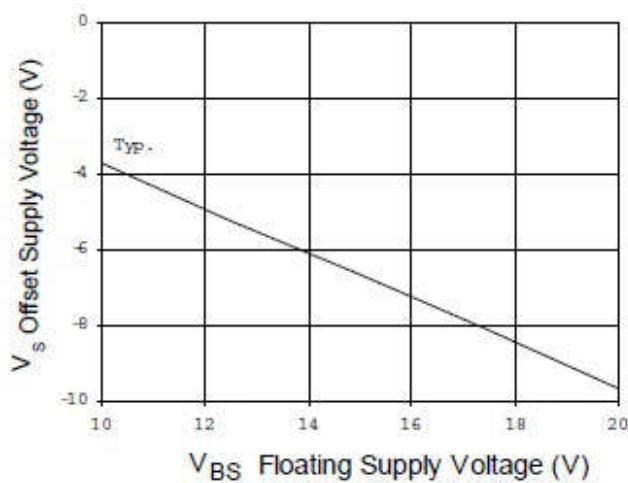
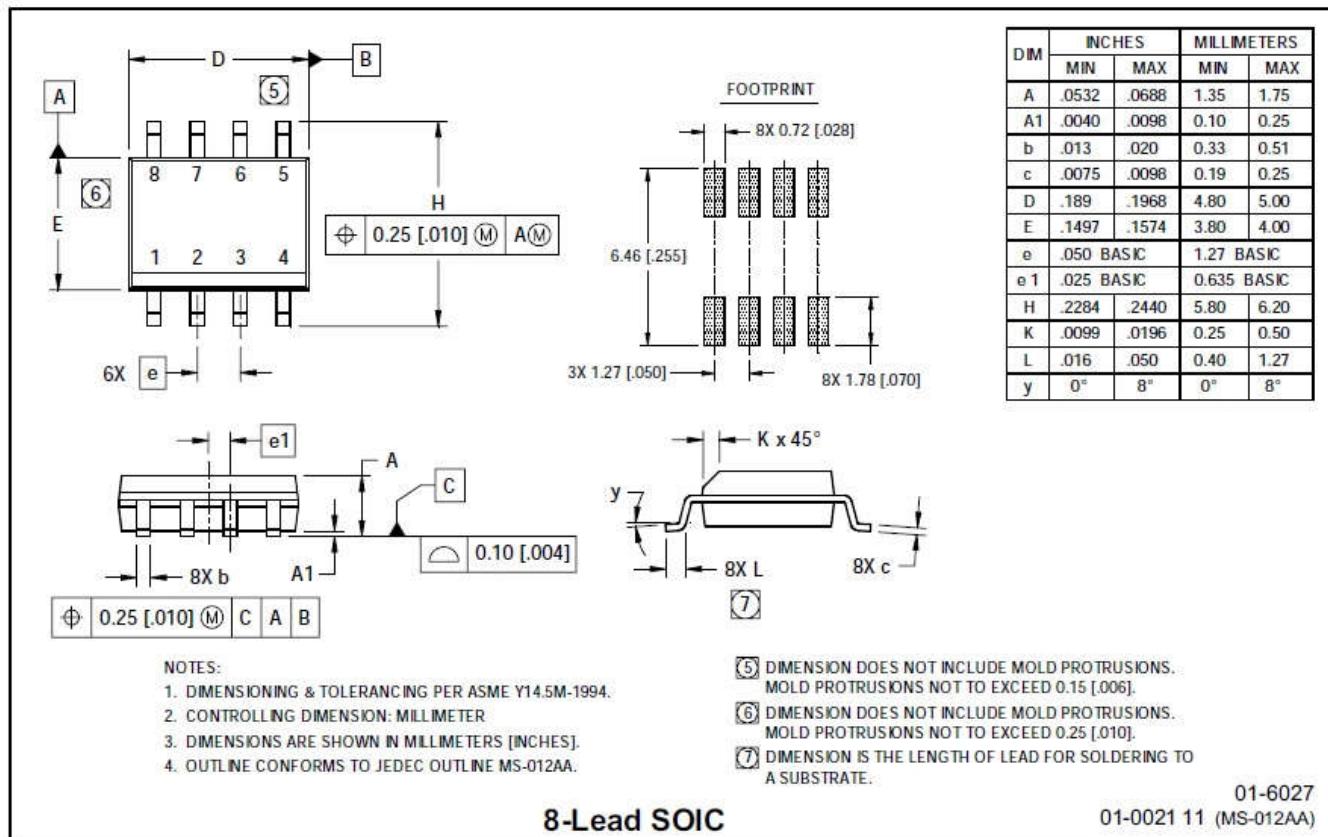
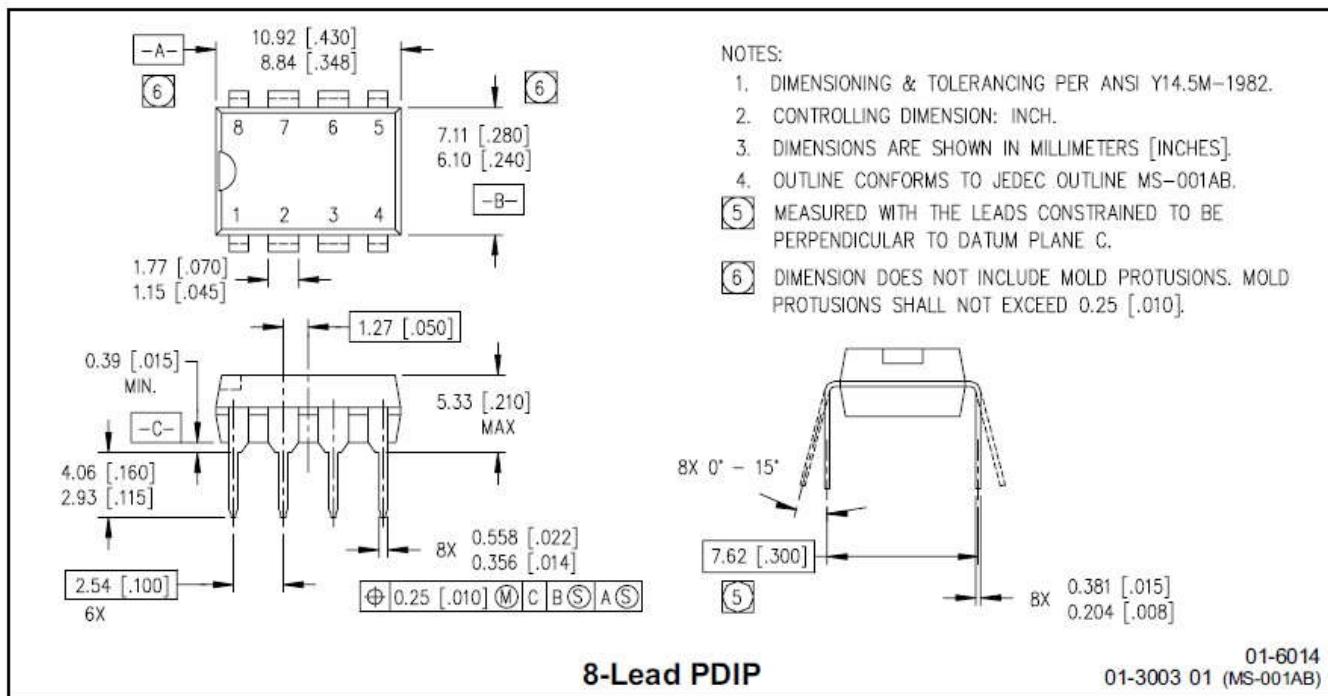
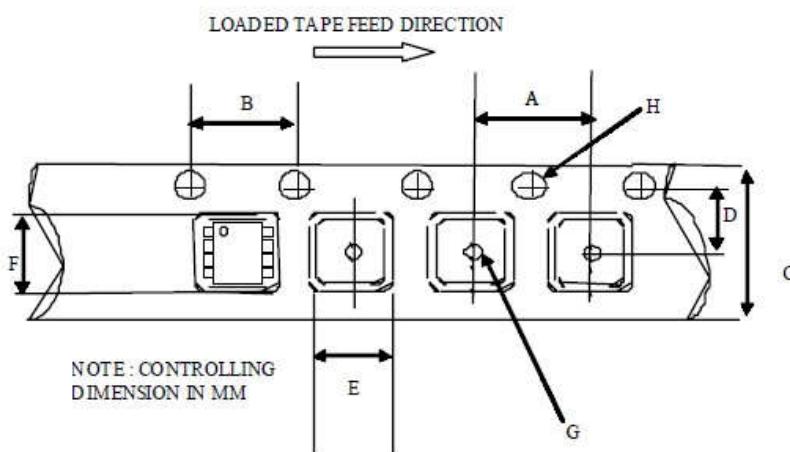


Figure 23. Maximum Vs Negative Offset
vs. Supply Voltage



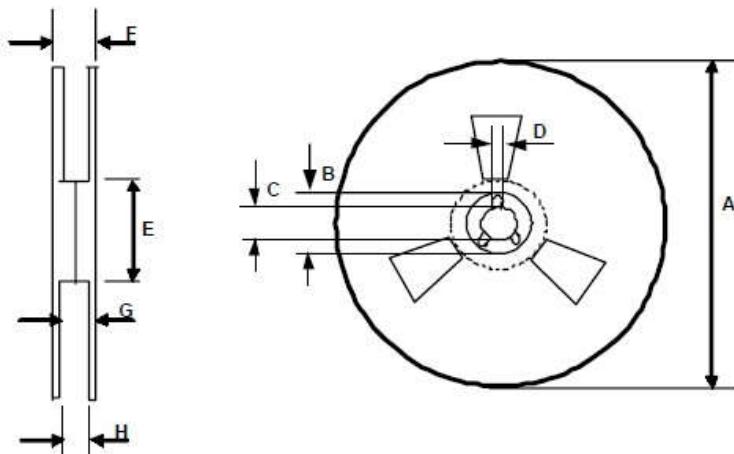
PACKAGE CASE OUTLINES



**Tape & Reel
8-lead SOIC**

CARRIER TAPE DIMENSION FOR 8SOICN

Code	Metric		Imperial	
	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
B	3.90	4.10	0.153	0.161
C	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
H	1.50	1.60	0.059	0.062



REEL DIMENSIONS FOR 8SOICN

Code	Metric		Imperial	
	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
B	20.95	21.45	0.824	0.844
C	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
H	12.40	14.40	0.488	0.566

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